				•
L Number	Hits	Search Text	DB	Time stamp
95	55571	control near gate	USPAT;	2004/05/04
			US-PGPUB;	14:39
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
97	1466709	memory	USPAT:	2004/05/04
			US-PGPUB;	14:39
			EPO; JPO;	11.55
			DERWENT:	
			IBM TDB	
100	273487	source and drain	USPAT;	2004 (05 (04)
	2/340/	Source and drain	1	2004/05/04
	-		US-PGPUB;	14:39
			EPO; JPO;	
	1		DERWENT;	Ī
	127944	/ A W A A A A A A A A A A A A A A A A A	IBM_TDB	0004405404
	12/944	(oxide near3 nitride near3 oxide) ONO	USPAT;	2004/05/04
	`	(oxide-nitride-oxide)	US-PGPUB;	14:40
		(oxide/nitride/oxide) (silicon near	EPO; JPO;	:
		oxide/silicon near nitride/silicon near	DERWENT;	
		oxide)	IBM_TDB	
101	4263	(control near gate) and (source and	USPAT;	2004/05/04
		drain) and memory and ((oxide hear3	US-PGPUB;	14:42
	٠.	nitride near3 oxide) ONO	EPO; JPO;	*
		(oxide-nitride-oxide)	DERWENT;	1
		(oxide/nitride/oxide) (silicon near	IBM_TDB	
	· '	oxide/silicon near nitride/silicon near		1
		oxide))		